

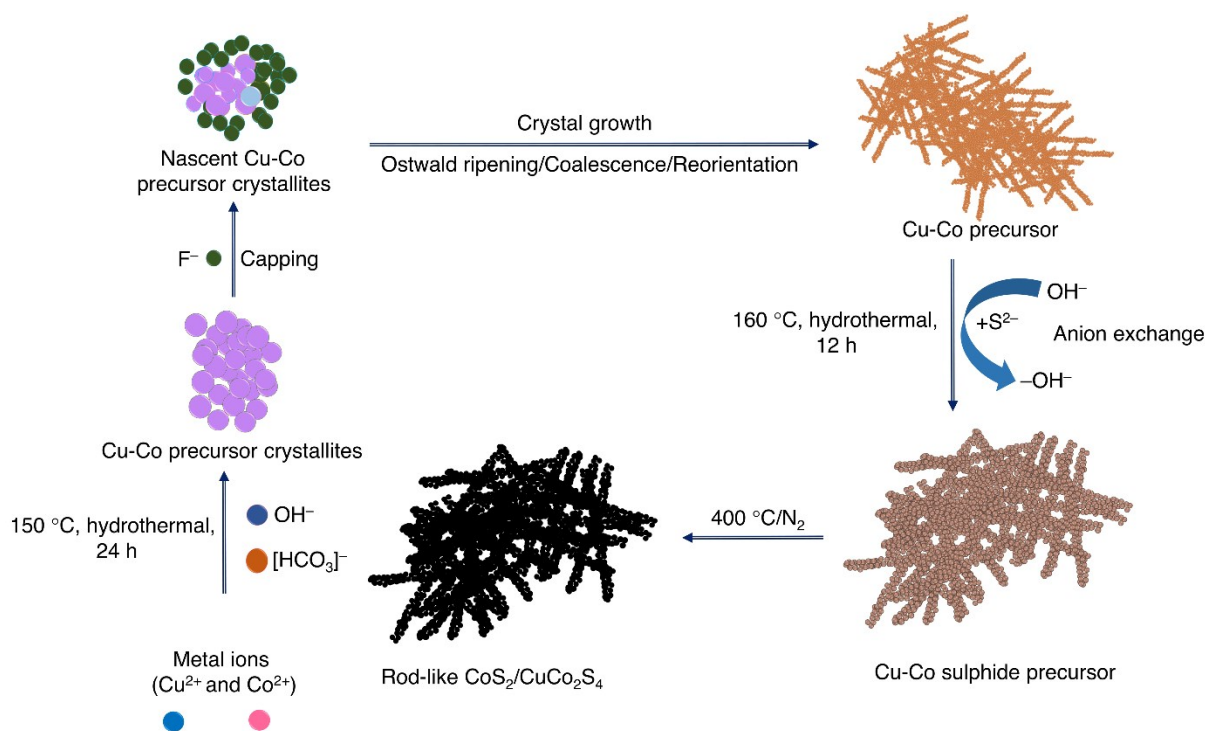
Supplementary Information

The rational design of hierarchical $\text{CoS}_2/\text{CuCo}_2\text{S}_4$ for three-dimensional all-solid-state hybrid supercapacitors with high energy density, rate efficiency, and operational stability

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Scheme S1 Plausible mechanism for the formation of $\text{CoS}_2/\text{CuCo}_2\text{S}_4$ rod-like microstructure.

Table S1. List of major peaks (binding energy) as shown in the survey XPS profile of $\text{CoS}_2/\text{CuCo}_2\text{S}_4$ and their corresponding attributions

Binding energy (eV)	Attribution
952.30	Cu 2p _{1/2}
932.40	Cu 2p _{3/2}
838.42	shake-up satellite
796.78	shake-up satellite
778.3	Co 2p
712.27	shake-up satellite
530.9	O 1s
284.15	C 1s
224.46	S 2s
160.76	S 2p
121.89	Cu 3s
102.5	Co 3s
74.99	Cu 3p
58.18	Co 3p

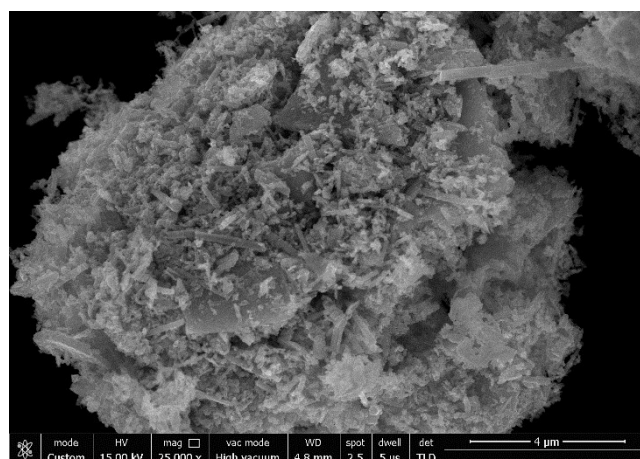


Fig. S1 FESEM image of $\text{CoS}_2/\text{CuCo}_2\text{S}_4$, which has been used for EDX elemental mapping.

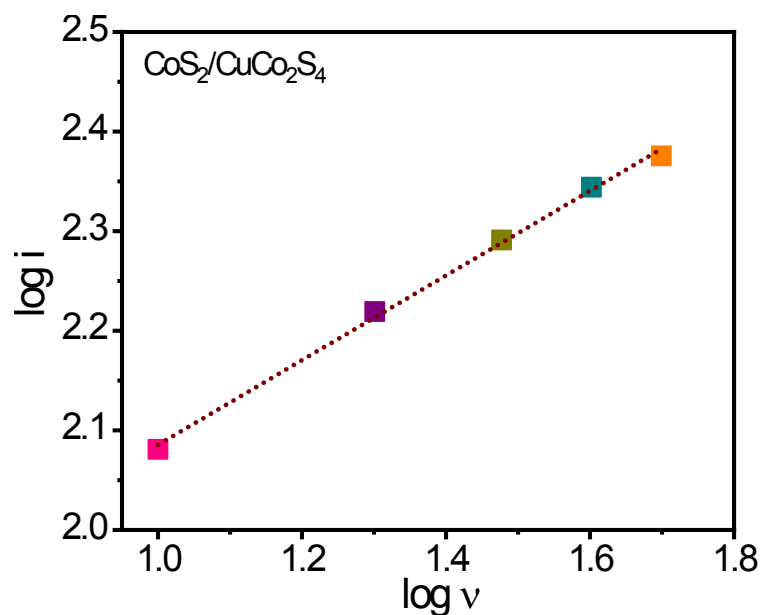


Fig. S2 Linear-fitted $\log \nu$ vs. $\log i$ plot of $\text{CoS}_2/\text{CuCo}_2\text{S}_4$

Table S2. Comparison of the specific capacitance and charge transfer resistance values of $\text{CoS}_2/\text{CuCo}_2\text{S}_4$ with reported CuCo_2S_4 -based materials.

Sl. No.	Sample Name	C_s @Current Density (3-Electrode Setup)	C_s @Scan Rate (3-Electrode Setup)	R_{ct} (Ω) from EIS (3-Electrode Setup)	Reference
1	CuCo_2S_4 dandelion-like	424 F g^{-1} @1 A g^{-1}	-	-	[s1]
2	CuCo_2S_4 @CNT	1690 F g^{-1} @1 A g^{-1}	-	-	[s2]
3	CuCo_2S_4 -rGO	525 F g^{-1} @1 A g^{-1} ; 425 F g^{-1} @5 A g^{-1} ; 370 F g^{-1} @10 A g^{-1} ; 326 F g^{-1} @15 A g^{-1} ; 303 F g^{-1} @20 A g^{-1}	665 F g^{-1} @ 7.5 mV s^{-1}	-	[s3]
4	CNTs@NC@ CuCo_2S_4	1604 F g^{-1} @1 A g^{-1} ; 1044 F g^{-1} @2 A g^{-1} ; 1000 F g^{-1} @5 A g^{-1} ; 955 F g^{-1} @10 A g^{-1} ; 896 F g^{-1} @20 A g^{-1}	-	135.6	[s4]
5	CuCo_2S_4 -HNN (hollow nano-needle arrays)	2163 F g^{-1} @6 A g^{-1}	-	-	[s5]
6	$\text{CuCo}_2\text{S}_4/\text{CNT}/\text{Graphene}$	504 F g^{-1} @10 A g^{-1}	-	-	[s6]

7	CuCo ₂ S ₄ nanowire	875 F g ⁻¹ @1 A g ⁻¹	-	1.96	[s7]
8	CuCo ₂ S ₄ nanorod array	1536 F g ⁻¹ @1 A g ⁻¹ ; 1295 F g ⁻¹ @5 A g ⁻¹ ; 1157 F g ⁻¹ @10 A g ⁻¹ ; 1026 F g ⁻¹ @20 A g ⁻¹	-	-	[s8]
9	CuCo ₂ S ₄ /GA (graphene aerogel)	668 F g ⁻¹ @1 A g ⁻¹ ; 620 F g ⁻¹ @2 A g ⁻¹ ; 588 F g ⁻¹ @5 A g ⁻¹ ; 535 F g ⁻¹ @10 A g ⁻¹ ; 480 F g ⁻¹ @20 A g ⁻¹	-	-	[s9]
10	CuCo ₂ S ₄ micro-sphere	516 F g ⁻¹ @10 A g ⁻¹	665 F g ⁻¹ @10 mV s ⁻¹ ; 482 F g ⁻¹ @50 mV s ⁻¹	0.26	[s10]
11	CuCo ₂ S ₄ nanoparticle	772 F g ⁻¹ @2 A g ⁻¹	-	-	[s11]
12	CuCo ₂ S ₄ ball-in-ball	442 F g ⁻¹ @0.5 A g ⁻¹	-	-	[s12]
13	CuCo ₂ S ₄ agglomerate nanoparticle	580 F g ⁻¹ @1 A g ⁻¹ ; 529 F g ⁻¹ @2 A g ⁻¹ ; 482 F g ⁻¹ @3 A g ⁻¹ ; 437 F g ⁻¹ @4 A g ⁻¹ ; 406 F g ⁻¹ @5 A g ⁻¹ ; 354 F g ⁻¹ @7 A g ⁻¹	-	5.65	[s13]
14	CuCo ₂ S ₄ microsphere	1566 F g ⁻¹ @2 A g ⁻¹	-	0.27	[s14]
15	CuCo ₂ S ₄ /NG (N-doped graphene)	1005 F g ⁻¹ @1 A g ⁻¹ ; 978 F g ⁻¹ @3 A g ⁻¹ ; 949 F g ⁻¹ @5 A g ⁻¹ ; 901 F g ⁻¹ @10 A g ⁻¹ ; 831 F g ⁻¹ @20 A g ⁻¹	-	-	[s15]
16	C@CuCo ₂ S ₄	854 F g ⁻¹ @1 A g ⁻¹ ; 774 F g ⁻¹ @3 A g ⁻¹ ; 681 F g ⁻¹ @5 A g ⁻¹ ; 597 F g ⁻¹ @7 A g ⁻¹ ; 485 F g ⁻¹ @10 A g ⁻¹	-	-	[s16]
17	CuCo ₂ S ₄ nanoparticles	449 F g ⁻¹ @1 A g ⁻¹ ; 443 F g ⁻¹ @1.5 A g ⁻¹ ; 433 F g ⁻¹ @3 A g ⁻¹ ; 401 F g ⁻¹ @5 A g ⁻¹	-	0.56	[s17]
18	GQD (graphene quantum dots)/CuCo ₂ S ₄	1725 F g ⁻¹ @0.1 A g ⁻¹	-	-	[s18]

19	N-doped C-coated CuCo ₂ S ₄	1228 F g ⁻¹ @1 A g ⁻¹ ; 1070 F g ⁻¹ @2 A g ⁻¹ ; 1003 F g ⁻¹ @3 A g ⁻¹ ; 933 F g ⁻¹ @5 A g ⁻¹ ; 864 F g ⁻¹ @10 A g ⁻¹ ; 784 F g ⁻¹ @20 A g ⁻¹	2002 F g ⁻¹ @5 mV s ⁻¹ ; 1831 F g ⁻¹ @10 mV s ⁻¹ ; 1535 F g ⁻¹ @ 20 mV s ⁻¹ ; 1168 F g ⁻¹ @50 mV s ⁻¹ ; 921 F g ⁻¹ @ 100 mV s ⁻¹	0.39	[s19]
20	CoS ₂ /CuCo ₂ S ₄	2438 F g ⁻¹ @2 A g ⁻¹ ; 1995 F g ⁻¹ @3 A g ⁻¹ ; 1730 F g ⁻¹ @4 A g ⁻¹ ; 1590 F g ⁻¹ @5 A g ⁻¹ ; 1492 F g ⁻¹ @6 A g ⁻¹	4653 F g ⁻¹ @10 mV s ⁻¹ ; 3618 F g ⁻¹ @20 mV s ⁻¹ ; 3007 F g ⁻¹ @ 30 mV s ⁻¹ ; 2552 F g ⁻¹ @40 mV s ⁻¹ ; 2169 F g ⁻¹ @ 50 mV s ⁻¹	0.23	This work

Table S3. Comparison of the energy density, power density and multiple-cycle capacitance retention of CoS₂/CuCo₂S₄||N-rGO ASSHSC device with reported CuCo₂S₄-based hybrid supercapacitor devices.

Sl. No.	Hybrid Supercapacitor Device	Energy Density (E_D ; W h Kg ⁻¹)	Power Density (P_D ; W Kg ⁻¹)	Capacitance Retention (%/No. of cycle)	Reference
1	CuCo ₂ S ₄ /CC AC	17.12	194.4	78.4 / 3,000	[s20]
2	CuCo ₂ S ₄ GA	22	1080	70.4 / 5,000	[s9]
3	CuCo ₂ S ₄ /CNT AC	23.2	402.7	85.7 / 10,000	[s21]
4	CuCo ₂ S ₄ /N,S-RGO N,S-RGO	10.8	400	88.9 / 5,000	[s22]
5	CuCo ₂ S ₄ @NiCo ₂ S ₄ AC	23.4	400	71 / 3,000	[s23]
6	CuCo ₂ S ₄ AC	15.0	422.5	94.7 / 5,000	[s17]
7	CuCo ₂ S ₄ AC-ASC	16	240	99.5 / 6,000	[s13]
8	CuCo ₂ S ₄ AC	22	405	62 / 20,000	[s1]
9	CoS ₂ /CuCo ₂ S ₄ N-rGO	32.4	4000	92.8 /10,000	This work

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